Product data sheet

1. General description

Silicon Carbide Schottky diode in a TO220-2L plastic package, designed for high frequency switched-mode power supplies.





2. Features and benefits

- · Highly stable switching performance
- High forward surge capability I_{FSM}
- · Extremely fast reverse recovery time
- · Superior in efficiency to Silicon Diode alternatives
- · Reduced losses in associated MOSFET
- Reduced EMI
- Reduced cooling requirements
- RoHS compliant

3. Applications

- · Power factor correction
- Telecom / Server SMPS
- UPS
- PV inverter
- PC Silverbox
- LED / OLED TV
- · Motor Drives

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Values			Unit	
Absolute	maximum rating						
V_{RRM}	repetitive peak reverse voltage			6	50		V
I _{F(AV)}	average forward current	$δ$ = 0.5 ; square-wave pulse; T_{mb} ≤ 110 °C; <u>Fig. 1</u> ; <u>Fig. 2</u> ; <u>Fig. 3</u>	12			А	
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static ch	aracteristics						
V_{F}	forward voltage	I _F = 12 A; T _j = 25 °C; <u>Fig. 5</u>		-	1.5	1.7	V
		I _F = 12 A; T _j = 150 °C; <u>Fig. 5</u>		-	1.8	2.1	V

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	mb	1/ Ld A
2	А	anode]	K A 001aaa020
mb	К	mounting base; connected to cathode		

6. Ordering information

Table 3. Ordering information

Type number	_	Orderable part number		Small packing	Package	Package
	name		method	quantity	version	issue date
NXPSC12650	TO220-2L	NXPSC126506Q	Tube	50	SOD59A	30-Mar-2015

7. Marking

Table 4. Marking codes

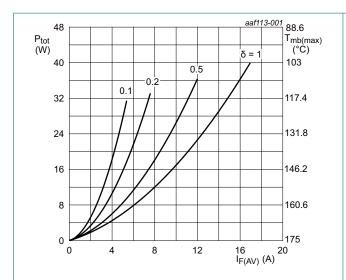
Type number	Marking codes
NXPSC12650	NXPSC 12650

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
V_{RRM}	repetitive peak reverse voltage		650	V
V_{RWM}	crest working reverse voltage		650	V
V_R	reverse voltage	DC	650	V
I _{F(AV)}	average forward current	$δ$ = 0.5; square-wave pulse; $T_{mb} \le 110$ °C; Fig. 1; Fig. 2; Fig. 3	12	А
I _{FRM}	repetitive peak forward current	$δ = 0.5$; $t_p = 25 \mu s$; $T_{mb} \le 110 °C$; square-wave pulse	24	А
I _{FSM}	non-repetitive peak	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	72	Α
	forward current	t_p = 10 μs; $T_{j(init)}$ = 25 °C; square-wave pulse	620	Α
l ² t	I ² t for fusing	sine-wave pulse; T _{j(init)} = 25 °C; t _p = 10 ms	26	A ² s
T _{stg}	storage temperature		-55 to 175	°C
T _j	junction temperature		175	°C



 $I_{F(AV)} = I_{F(RMS)} \times \sqrt{\delta}$ $V_o = 0.740 \text{ V}; R_s = 0.0955 \Omega$

Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values

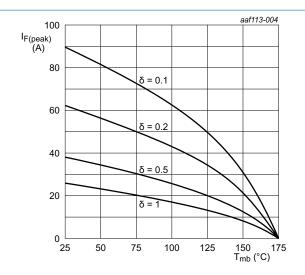


Fig. 2. Current derating as a function of mounting base temperature

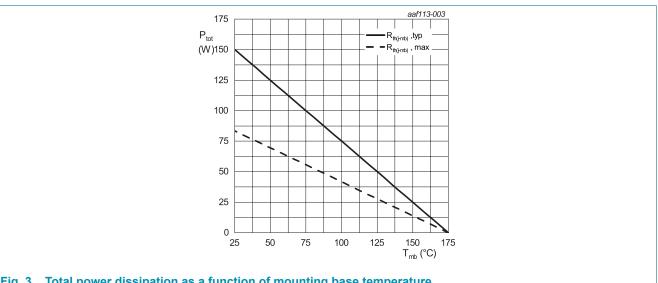


Fig. 3. Total power dissipation as a function of mounting base temperature

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{\text{th(j-mb)}}$	thermal resistance from junction to mounting base	with heatsink compound; Fig. 4	-	1.0	1.8	K/W
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient free air	in free air	-	60	-	K/W

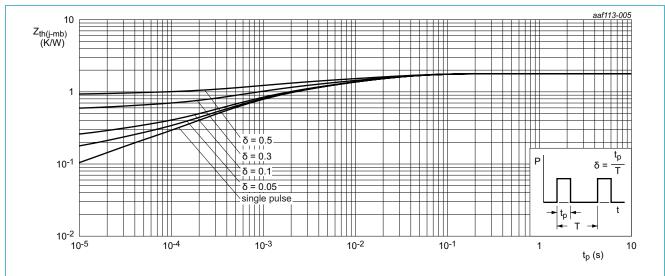
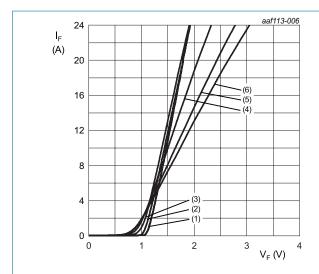


Fig. 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					1
V_{F}	forward current	I _F = 12 A; T _j = 25 °C; <u>Fig. 5</u>	-	1.5	1.7	V
		I _F = 12 A; T _j = 150 °C; <u>Fig. 5</u>	-	1.8	2.1	V
I _R	reverse current	V _R = 650 V; T _j = 25 °C; <u>Fig. 6</u>	-	-	80	μA
		V _R = 650 V; T _j = 150 °C; <u>Fig. 6</u>	-	-	320	μA
Dynamic	characteristics					
Q _r	recovered charge	$I_F = 12 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	18	-	nC
C _d	diode capacitance	f = 1 MHz; V _R = 1 V; T _j = 25 °C	-	380	-	pF
		f = 1 MHz; V _R = 300 V; T _j = 25 °C	-	60	-	pF
		f = 1 MHz; V _R = 600 V; T _j = 25 °C	-	58	-	pF
E _{as}	non-repetitive	$I_R = 6 \text{ A}; L = 5 \text{ mH}; T_{j(init)} = 25 \text{ °C}$	90	-	-	mJ
	avalanche energy					



 $V_o = 0.740 \text{ V}; R_s = 0.0955 \Omega$

(1) $T_i = -55$ °C; typical values

(2) $T_j = 0$ °C; typical values

(3) T_j = 25 °C; typical values (4) T_j = 100 °C; typical values

(5) T_i = 150 °C; typical values

(6) T_i = 175 °C; typical values Fig. 5. Forward current as a function of forward

voltage; typical values

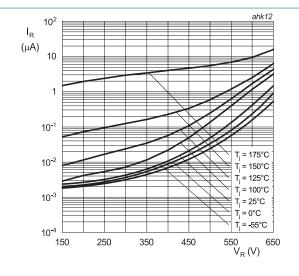


Fig. 6. Reverse leakage current as a function of reverse voltage; typical value

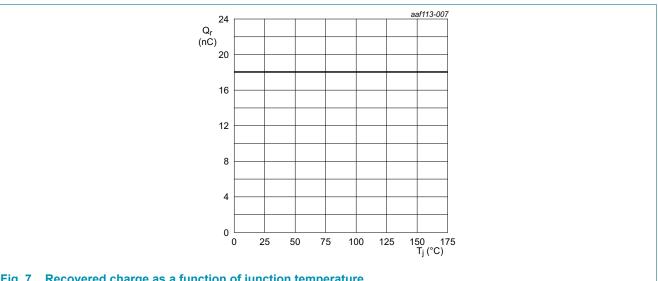
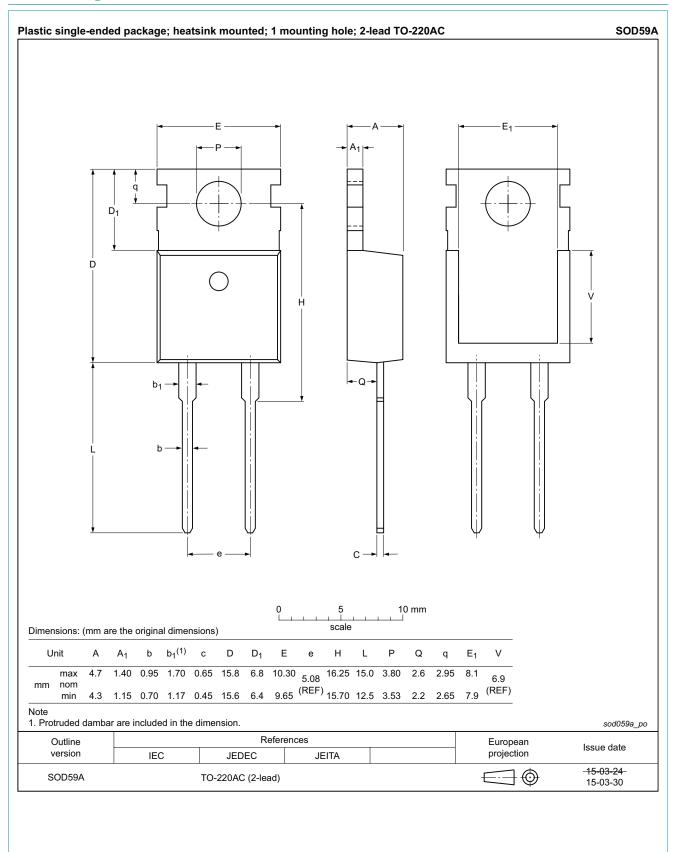


Fig. 7. Recovered charge as a function of junction temperature

11. Package outline



12. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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